

MAGNETIC FIELD ANGLE SENSOR

Description

The ZMT32 is a thin film permalloy magnetic field sensor, which contains two galvanic isolated Wheatstone Bridges for precision angle measurement applications under low field conditions. This angle sensor is based on the anisotropic magnetoresistive effect (AMR). The two internal (V_{CC1}, V_{CC2}) bridges enclose a relative sensitive angle of 45 degrees. The input field is a rotating magnetic field in the chip plane (parallel to the surface of package). This rotating field will make available two independent sinusoidal output signals with the following relationship

$$\frac{V_{O2}}{V_{O1}} = \frac{Sin(2\alpha)}{Cos(2\alpha)} = Tan(2\alpha)$$

where α = angle between sensor axis and field direction

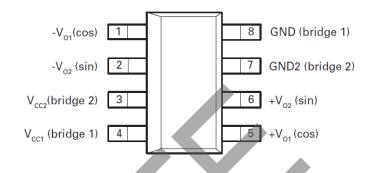
The precise ZMT32 works with low field applications (H_{rot} = 8 to 25kA/m), much lower than similar devices. The ultimate output signal quality depends on the external magnetic material and on the mechanical realization.

The ZMT32 is a passive part and the Arc-Tangent interpolation needs external signal processing. Typical areas of application are angle and speed measurement.

Features

- contactless angle measurement up to 180°
- flexible measuring solutions for moved systems
- · stable operation over long time
- high temperature range up to +160°C
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/quality/product-definitions/

Pin Assignments



Applications

- angle and angular velocity measuring systems
- absolute angle and angle change
- automotive electronic (steering, throttle control, pedal positioning, etc
- contactless rotary switches and potentiometer
- automatic adjustment



Absolute Maximum Ratings

Parameter	Symbol	Limit U	Jnit
Supply Voltages	V _{cc1} and V _{cc2}	10	V
Single Bridge Current	I _{cc1} or I _{cc2}	4 r	mA
Operating Temperature Range	T _A	-40 to +160	°C
Storage Temperature Range	T _{stg}	-55 to +175	°C

Recommended Operating Conditions

Symbol	Parameter	Min	Тур	Max	Unit
V _{cc1} , V _{cc2}	Supply Voltages		5	8.5	V
H _{rot}	Applied Magnetic Field Strength	8	25		kA/m



Electrical Characteristics

General test conditions (unless otherwise noted)

 $T_{A} = +23 \pm 5^{\circ} \text{C}, \ V_{CC1} = V_{CC2} = +5 \text{V}, \ H_{ROT} = 25 \text{kA/m}^{(\dagger)}, \ k = 100 \cdot (V_{PO1}/V_{PO2}) \ with \ V_{CC1} = V_{CC2} = +5 \text{V}, \ H_{ROT} = 25 \text{kA/m}^{(\dagger)}, \ k = 100 \cdot (V_{PO1}/V_{PO2}) \ with \ V_{CC1} = V_{CC2} = +5 \text{V}, \ H_{ROT} = 25 \text{kA/m}^{(\dagger)}, \ k = 100 \cdot (V_{PO1}/V_{PO2}) \ with \ V_{CC1} = V_{CC2} = +5 \text{V}, \ H_{ROT} = 25 \text{kA/m}^{(\dagger)}, \ k = 100 \cdot (V_{PO1}/V_{PO2}) \ with \ V_{CC1} = V_{CC2} = +5 \text{V}, \ H_{ROT} = 25 \text{kA/m}^{(\dagger)}, \ k = 100 \cdot (V_{PO1}/V_{PO2}) \ with \ V_{CC1} = V_{CC2} = +5 \text{V}, \ H_{ROT} = 25 \text{kA/m}^{(\dagger)}, \ k = 100 \cdot (V_{PO1}/V_{PO2}) \ with \ V_{CC1} = V_{CC2} = +5 \text{V}, \ H_{ROT} = 25 \text{kA/m}^{(\dagger)}, \ k = 100 \cdot (V_{PO1}/V_{PO2}) \ with \ V_{CC1} = V_{CC2} = +5 \text{V}, \ H_{ROT} = 25 \text{kA/m}^{(\dagger)}, \ k = 100 \cdot (V_{PO1}/V_{PO2}) \ with \ V_{CC1} = V_{CC2} = +5 \text{V}, \ H_{ROT} = 25 \text{kA/m}^{(\dagger)}, \ k = 100 \cdot (V_{PO1}/V_{PO2}) \ with \ V_{CC1} = V_{CC2} = +5 \text{V}, \ H_{ROT} = 25 \text{kA/m}^{(\dagger)}, \ k = 100 \cdot (V_{PO1}/V_{PO2}) \ with \ V_{CC1} = V_{CC2} = +5 \text{V}, \ H_{ROT} = 25 \text{kA/m}^{(\dagger)}, \ k = 100 \cdot (V_{PO1}/V_{PO2}) \ with \ V_{CC1} = V_{CC2} = +5 \text{V}, \ H_{ROT} = 25 \text{kA/m}^{(\dagger)}, \ k = 100 \cdot (V_{PO1}/V_{PO2}) \ with \ V_{CC1} = V_{CC2} = +5 \text{V}, \ H_{ROT} = 25 \text{kA/m}^{(\dagger)}, \ k = 100 \cdot (V_{PO1}/V_{PO2}) \ with \ V_{CC1} = V_{CC2} = +5 \text{V}, \ H_{ROT} = 25 \text{kA/m}^{(\dagger)}, \ k = 100 \cdot (V_{PO1}/V_{PO2}) \ with \ V_{CC2} = V_{CC2} = +5 \text{V}, \ H_{ROT} = 25 \text{kA/m}^{(\dagger)}, \ k = 100 \cdot (V_{PO1}/V_{PO2}) \ with \ V_{CC2} = V_{CC2} = +5 \text{V}, \ H_{ROT} = 25 \text{kA/m}^{(\dagger)}, \ k = 100 \cdot (V_{PO1}/V_{PO2}) \ with \ V_{CC2} = V_{CC2} = +5 \text{V}, \ H_{ROT} = 25 \text{kA/m}^{(\dagger)}, \ k = 100 \cdot (V_{PO1}/V_{PO2}) \ with \ V_{CC2} = V_{CC2} = +5 \text{V}, \ H_{ROT} = 25 \text{kA/m}^{(\dagger)}, \ k = 100 \cdot (V_{PO1}/V_{PO2}) \ with \ V_{CC2} = V_{CC2} = +5 \text{V}, \ H_{ROT} = 25 \text{kA/m}^{(\dagger)}, \ k = 100 \cdot (V_{PO1}/V_{PO2}) \ with \ V_{CC2} = V_{CC2} = 100 \cdot (V_{CC2}/V_{CC2}) \ with \ V_{CC2} = V_{CC2} = 100 \cdot (V_{CC2}/V_{CC2}) \ with \ V_{CC2} = V_{CC2} = 100 \cdot (V_{CC2}/V_{CC2}) \ wi$

SYMBOL	PARAMETER	CONDITIONS		MIN	TYP (*)	MAX	UNIT	
$S_{\alpha 1}$ or $S_{\alpha 2}$	Sensitivities (zero crossing)	α1=135°, α2=0°			0.35		mV/V/deg	
V _{PO1} or V _{PO2}	Peak Output Voltages (sinusoidal signals)			40	50	60	mV	
k	Amplitude bridge matching			99.77	100	100.23	%	
TCk	Temperature coefficient of amplitude bridge matching	T _A = -40 to	o +160°C	-0.008		+0.008	%/K	
R _{B1}			T _A = -40°C	2017		3040		
or	Bridge resistances	no H _{ROT}	T _A = 23°C	2500	3000	3600	Ω	
R _{B2}		No record	T _A = +160°C	3345		5114		
TCR _B B	TC of Bridge Resistances			+0.28	+0.32	+0.36	%/K	
Δ			T _A = -40°C	19.2		30.4	mV/V	
$\Delta V_{O1}/V_{CC1}^{A}$	Peak to peak output swing		T _A = 23°C	16	20	24		
or			T _A = +160°C	6.7		13.4		
$\Delta V_{O2}/V_{CC2}^A$		$H_{ROT} = 8 \text{ kA/m(t)}$	T _A = 23°C	16	20	24		
TCV _O B	TC of peak to peak output swing			-0.35	-0.32	-0.28	%/K	
\/ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \			T _A = -40°C	-1.25		+1.25		
V _{OFF1} /V _{CC1} A	Output offset voltage		T _A = +160°C	-1.55		+1.55	mV/V	
V _{OFF2} /V _{CC2} A		H _{ROT} = 8 kA/m ^(†)	T _A = 23°C	-1	0	+1	IIIV/V	
VOFF2/VCC2		no H _{ROT}	1 A - 23 G	-2	0	+2		
TCV _{OFF} B	TC of output offset voltage			-4	0	+4	μV/V/K	
$\Delta \alpha^{A}$	Angular Inaccuracy				0.05	0.2	deg	
41 1Δ	Angular hystoresis					0.1	deg	
ΔαH ^A	Angular hysteresis	H _{ROT} = 8 kA/m(†)				0.5 (‡)	deg	
I _{iso1-2}	Isolation Bridge Current	no H _{ROT}		0		0.1	μA	

NOTES

- (*) Typical values apply to an ambient temperature of 23°C
- (†) See point "Magnetic Field Tests" below
- (‡) The accurate control of this parameter (Lim_{max}=0.1deg, H_{ROT}=25kA/m) takes place by means of sample tests



Electrical Characteristics (continued)

A: Output characteristic definitions

B: Temperature coefficient (TC) equations

$$\begin{split} T_1 &= -25^{\circ}\text{C}, & T_0 &= +25^{\circ}\text{C}, & T_2 &= +125^{\circ}\text{C} \\ T\text{CV}_O &= \frac{1}{T_2 - T_1} \times \frac{\frac{\Delta V_O}{V_{CC}}(T_2) - \frac{\Delta V_O}{V_{CC}}(T_1)}{\frac{\Delta V_O}{V_{CC}}(T_0)} \times 100\% & \\ & \text{where} & \frac{\Delta V_O}{V_{CC}}(T_n) & \text{is the peak-peak output voltage at temperature } T_n \end{split}$$

$$\begin{aligned} \text{TCR}_B &= \frac{1}{T_2 - T_1} \times \frac{R_B(T_2) - R_B(T_1)}{R_B(T_0)} \times 100\% \\ \text{TCV}_{OFF} &= \frac{V_{OFF(T2)} - V_{OFF(T1)}}{(T_2 - T_1)} \end{aligned} \quad \text{where} \quad R_B(T_n) \text{ is the bridge resistance at temperature } T_n$$

Magnetic field tests

For these tests a rotating magnetic field is generated and the output signals of both bridges are measured at four different field angles for right rotation as well as for left rotation. Using these measured output signals the diameter and the center coordinates of the best circle are calculated. They correspond to the output voltage range and the offset voltage. Furthermore the field angles for both rotation directions and angular hysteresis are calculated

[measured angle] =
$$\alpha$$
 = arctan $\frac{V_{O2}}{V_{O1}}$

Method

The data pairs are transformed onto a unit circle starting from their position in the data collection for determining direction information or angle information.

It must be evaluated with four pair values (cos, sin) on a right rotation (magnetic field rotation) and four pair values (cos, sin) on a left rotation (magnetic field rotation).



Electrical Characteristics (continued)

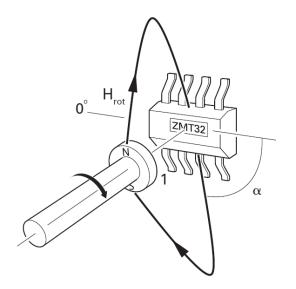
The field rotation steps are:

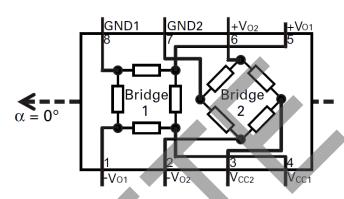
- → start in 180° position
 - § right rotation to 22.5° with measurement of sensor outputs
 - § right rotation to 67.5° with measurement of sensor outputs
 - § right rotation to 112.5° with measurement of sensor outputs
 - § right rotation to 157.5° with measurement of sensor outputs
 - § right rotation to 0° (360°), stop, reversal
 - § left rotation to 157.5° with measurement of sensor outputs
 - § left rotation to 112.5° with measurement of sensor outputs
 - § left rotation to 67.5° with measurement of sensor outputs
 - § left rotation to 22.5° with measurement of sensor outputs, end position

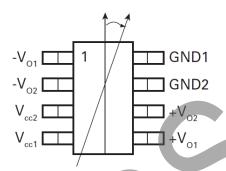
General description of tests with external magnetic field.



Operating Principle







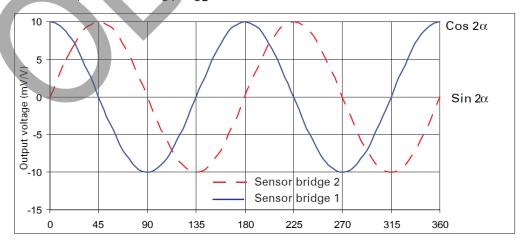
When a common-magnetic field is applied through the ZMT32 the 2 internal magneto-resistive bridges are affected slightly differently due to their 45° rotation to one another. This 45° rotation enables the ZMT32 to determine angular position, of a rotating magnetic field.

When a rotating magnetic field is applied to the ZMT32 it will output 2 sinusoidal voltages that are:

- proportional to the field strength applied
- proportional to the supply voltage applied,
- rotating at twice the angular position
- 90° apart (as seen below).

By taking the arcTan of the ratio of $V_{\rm O2}$ to $V_{\rm O1}$ the angular position of the magnetic field can be determined.

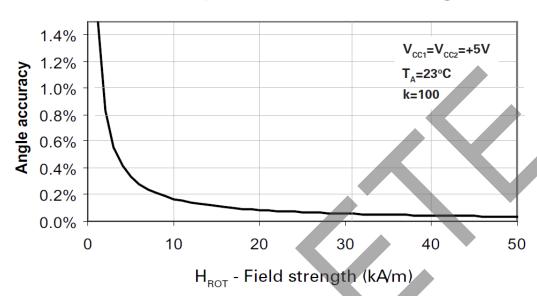
Characteristic output curves V_{O1}, V_{O2}



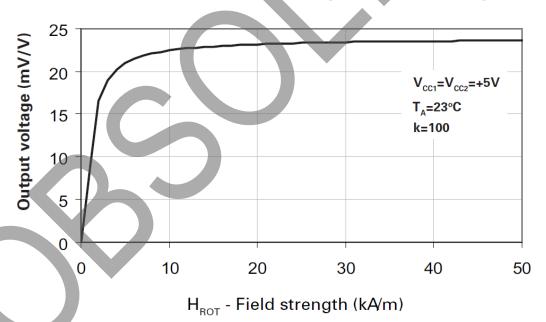


Typical Characteristics

Accuracy variance with field strength



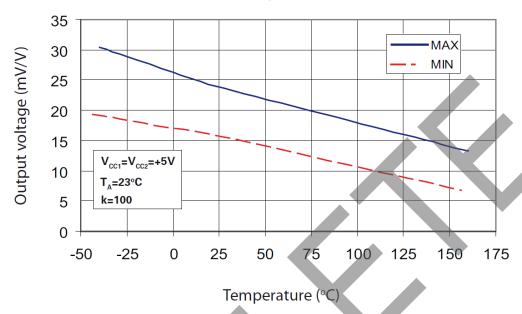
Output variance with magnetic field strength



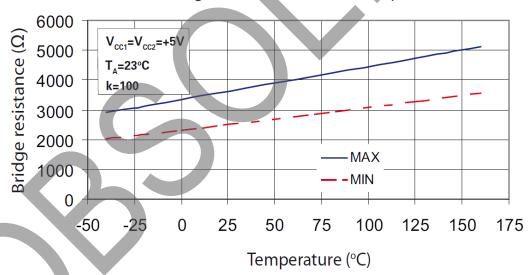


Typical Characteristics (continued)

Output voltage versus temperature

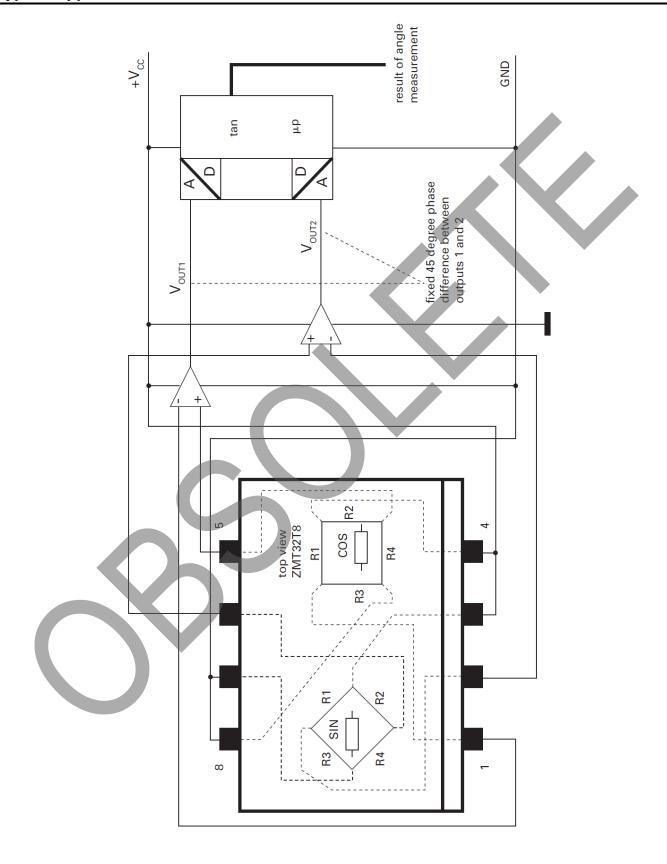


Bridge resistance versus temperature





Typical Application





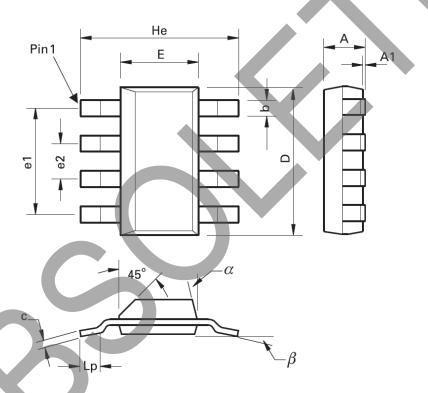
Ordering Information

Device	Reel size	Tape width	Quantity	Device
	(Inches)	(mm)	per reel	marking
ZMT32TA	7	12	1,000	ZETEX ZMT32

Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

(1) Package Type: SM-8



DIM	Millimeters			Inches		DIM	N	Millimeters		Inches			
	Min.	Max.	Тур.	Min.	Max.	Тур.		Min.	Max.	Тур.	Min.	Max.	Тур.
Α	-	1.7	-	-	0.067	-	e1	-	-	4.59	-	-	0.1807
A1	0.02	0.1	-	0.0008	0.004	-	e2	-	-	1.53	-	-	0.0602
b	-	-	0.7	-	-	0.0275	He	6.7	7.3	-	0.264	0.287	-
С	0.24	0.32	-	0.009	0.013	-	Lp	0.9	-	-	0.035	-	-
D	6.3	6.7	-	0.248	0.264	-	α	-	15°	-	-	15°	-
Е	3.3	3.7	-	0.130	0.145	-	β	-	-	10°	-	-	10°

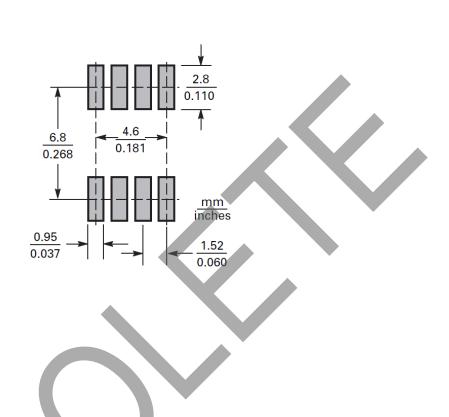
Note: Controlling dimensions are in millimeters. Approximate dimensions are provided in inches



Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

(1) Package Type: SM-8





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